

# MFQ930C

# MFQ960C

# MFQ990C

**CASE 632-02, STYLE 1  
TO-116**

**QUAD  
DUAL-IN-LINE  
TMOS**

**N-CHANNEL — ENHANCEMENT**

## MAXIMUM RATINGS

Rating	Symbol	MFQ930C	MFQ960C	MFQ990C	Unit
Drain-Source Voltage	$V_{DS}$	35	60	90	Vdc
Drain-Gate Voltage	$V_{DG}$	35	60	90	Vdc
Gate-Source Voltage	$V_{GS}$		$\pm 30$		Vdc
Drain Current Continuous (1) Pulsed (2)	$I_D$ $I_{DM}$		2.0 3.0		Adc
				Each Transistor	Total Device
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate Above $25^\circ\text{C}$	$P_D$	0.5 17.0	2.0 66.6		Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$		-55 to +150		$^\circ\text{C}$

Refer to MFE930 for graphs.

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)

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Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ( $V_{GS} = 0, I_D = 10 \mu\text{A}$ )	$V_{(BR)DSX}$	35 60 90	— — —	— — —	Vdc
Gate Reverse Current ( $V_{GS} = 15 \text{ Vdc}, V_{DS} = 0$ )	$I_{GSS}$	—	—	50	nAdc

### ON CHARACTERISTICS\*

Zero-Gate-Voltage Drain Current ( $V_{DS} = \text{Maximum Rating}, V_{GS} = 0$ )	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
Gate Threshold Voltage ( $I_D = 1.0 \text{ mA}, V_{DS} = V_{GS}$ )	$V_{GS(\text{Th})}$	1.0	—	3.5	Vdc
Drain-Source On-Voltage ( $V_{GS} = 10 \text{ V}$ ) ( $I_D = 0.5 \text{ A}$ )	$V_{DS(on)}$	— — —	0.4 0.6 0.6	0.7 0.8 1.0	Vdc
( $I_D = 1.0 \text{ A}$ )	MFO930C MFO960C MFO990C	— — —	0.9 1.2 1.2	1.4 1.7 2.0	
( $I_D = 2.0 \text{ A}$ )	MFO930C MFO960C MFO990C	— — —	2.2 2.8 2.8	3.0 3.5 4.0	
Static Drain-Source On Resistance ( $V_{GS} = 10 \text{ Vdc}, I_D = 1.0 \text{ Adc}$ )	$r_{DS(on)}$	— — —	0.9 1.2 1.2	1.4 1.7 2.0	Ohms
On-State Drain Current ( $V_{DS} = 25 \text{ V}, V_{GS} = 10 \text{ V}$ )	$I_{D(on)}$	1.0	2.0	—	Amps

### SMALL-SIGNAL CHARACTERISTICS

Input Capacitance ( $V_{DS} = 25 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz}$ )	$C_{iss}$	—	60	70	pF
Reverse Transfer Capacitance ( $V_{DS} = 25 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz}$ )	$C_{rss}$	—	13	18	pF
Output Capacitance ( $V_{DS} = 25 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz}$ )	$C_{oss}$	—	49	60	pF
Forward Transconductance ( $V_{DS} = 25 \text{ V}, I_D = 0.5 \text{ A}$ )	$g_{fs}$	200	380	—	mmhos

### SWITCHING CHARACTERISTICS

Turn-On Time	$t_{on}$	—	7.0	15	ns
Turn-Off Time	$t_{off}$	—	7.0	15	ns